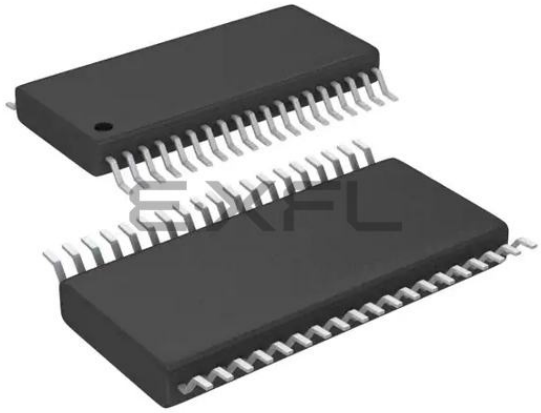
Infineon Technologies - XMC1100T038F0016ABXUMA1 Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	26
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	38-TFSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-38-9
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t038f0016abxuma1

Edition 2016-08

Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (**www.infineon.com**).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

XMC1100 Data Sheet

Revision History: V1.7 2016-08

Previous Version: V1.6	
Page	Subjects
many	Added XMC™ trademark
Page 23	Removed ADC channels from Port I/O Functions table, which are not available in XMC1100 (G1CH0, G1CH2, G1CH3, G1CH4).
Page 36	Removed auxiliary V_{REFGND} for G1CH0, as this channel is not available in XMC1100.
Page 36	Adjusted ADC sample time and sample rate to configurable limits.
Page 46	Flash Memory Parameters Table: • Erase time per page parameter is renamed to Erase time per page / sector. • Erase cycles parameter is renamed to include test condition of sum of page and sector erase cycles. • Added parameter for fixed wait states configuration.

Trademarks

C166™, TriCore™, XMC™ and DAVE™ are trademarks of Infineon Technologies AG.

ARM®, ARM Powered® and AMBA® are registered trademarks of ARM, Limited.

Cortex®, CoreSight™, ETM™, Embedded Trace Macrocell™ and Embedded Trace Buffer™ are trademarks of ARM, Limited.

We Listen to Your Comments

Is there any information in this document that you feel is wrong, unclear or missing? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

mcdocu.comments@infineon.com

Table 4 XMC1100 Chip Identification Number (cont'd)

Derivative	Value	Marking
XMC1100-Q040F0032	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00009000 201ED083$_H$	AB
XMC1100-Q040F0064	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00011000 201ED083$_H$	AB

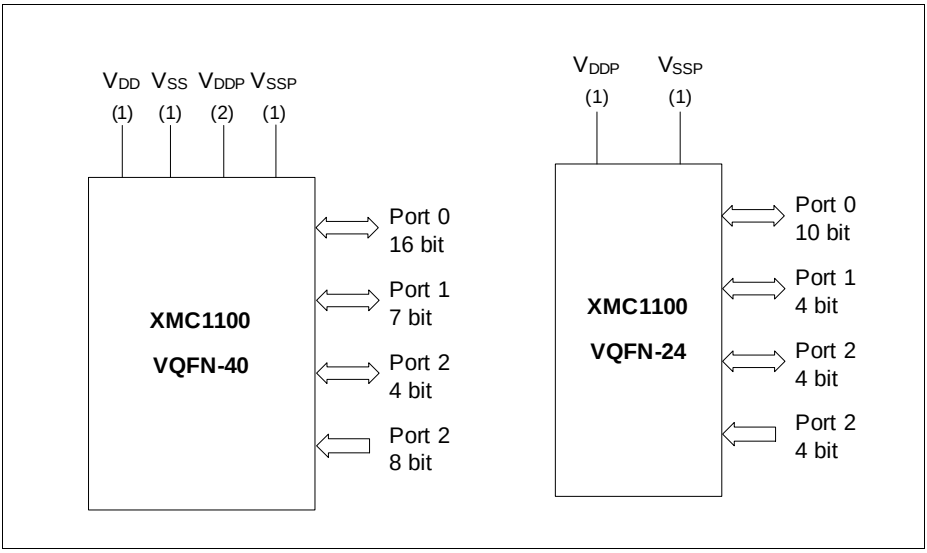


Figure 3 XMC1100 Logic Symbol for VQFN-24 and VQFN-40

Table 6 Package Pin Mapping (cont'd)

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.13	38	32	22	-	STD_INOUT	
P0.14	39	33	23	13	STD_INOUT	
P0.15	40	34	24	14	STD_INOUT	
P1.0	22	16	14	-	High Current	
P1.1	21	15	13	-	High Current	
P1.2	20	14	12	-	High Current	
P1.3	19	13	11	-	High Current	
P1.4	18	12	-	-	High Current	
P1.5	17	11	-	-	High Current	
P1.6	16	-	-	-	STD_INOUT	
P2.0	1	35	1	15	STD_INOUT/ AN	
P2.1	2	36	2	-	STD_INOUT/ AN	
P2.2	3	37	3	-	STD_IN/AN	
P2.3	4	38	-	-	STD_IN/AN	
P2.4	5	1	-	-	STD_IN/AN	
P2.5	6	2	-	-	STD_IN/AN	
P2.6	7	3	4	16	STD_IN/AN	
P2.7	8	4	5	1	STD_IN/AN	
P2.8	9	5	5	1	STD_IN/AN	
P2.9	10	6	6	2	STD_IN/AN	
P2.10	11	7	7	3	STD_INOUT/ AN	
P2.11	12	8	8	4	STD_INOUT/ AN	
VSS	13	9	9	5	Power	Supply GND, ADC reference GND
VDD	14	10	10	6	Power	Supply VDD, ADC reference voltage/ ORC reference voltage

Table 9 Port I/O Functions

Function	Outputs							Inputs						
	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	Input	Input	Input	Input	Input	Input	Input
P1.1	VADC0.EMUX00	CCU40.OUT1				USIC0_CH0.DOUT0	USIC0_CH1.SELO0					USIC0_CH0.DX0D	USIC0_CH0.DX1D	USIC0_CH1.DX2E
P1.2	VADC0.EMUX01	CCU40.OUT2					USIC0_CH1.DOUT0					USIC0_CH1.DX0B		
P1.3	VADC0.EMUX02	CCU40.OUT3				USIC0_CH1.SCLKOUT	USIC0_CH1.DOUT0					USIC0_CH1.DX0A	USIC0_CH1.DX1A	
P1.4	VADC0.EMUX10	USIC0_CH1.SCLKOUT				USIC0_CH0.SELO0	USIC0_CH1.SELO1					USIC0_CH0.DX5E	USIC0_CH1.DX5E	
P1.5	VADC0.EMUX11	USIC0_CH0.DOUT0				USIC0_CH0.SELO1	USIC0_CH1.SELO2					USIC0_CH1.DX5F		
P1.6	VADC0.EMUX12	USIC0_CH1.DOUT0		USIC0_CH0.SCLKOUT		USIC0_CH0.SELO2	USIC0_CH1.SELO3			USIC0_CH0.DX5F				
P2.0	ERU0.PDOUT3	CCU40.OUT0	ERU0.GOUT3			USIC0_CH0.DOUT0	USIC0_CH0.SCLKOUT		VADC0.G0CH5		ERU0.0B0	USIC0_CH0.DX0E	USIC0_CH0.DX1E	USIC0_CH1.DX2F
P2.1	ERU0.PDOUT2	CCU40.OUT1	ERU0.GOUT2			USIC0_CH0.DOUT0	USIC0_CH1.SCLKOUT		VADC0.G0CH6		ERU0.1B0	USIC0_CH0.DX0F	USIC0_CH1.DX3A	USIC0_CH1.DX4A
P2.2									VADC0.G0CH7		ERU0.0B1	USIC0_CH0.DX3A	USIC0_CH0.DX4A	USIC0_CH1.DX5A
P2.3									VADC0.G1CH5		ERU0.1B1	USIC0_CH0.DX5B	USIC0_CH1.DX3C	USIC0_CH1.DX4C
P2.4									VADC0.G1CH6		ERU0.0A1	USIC0_CH0.DX3B	USIC0_CH0.DX4B	USIC0_CH1.DX5B
P2.5									VADC0.G1CH7		ERU0.1A1	USIC0_CH0.DX5D	USIC0_CH1.DX3E	USIC0_CH1.DX4E
P2.6									VADC0.G0CH0		ERU0.2A1	USIC0_CH0.DX3E	USIC0_CH0.DX4E	USIC0_CH1.DX5D
P2.7									VADC0.G1CH1		ERU0.3A1	USIC0_CH0.DX5C	USIC0_CH1.DX3D	USIC0_CH1.DX4D
P2.8									VADC0.G0CH1		ERU0.3B1	USIC0_CH0.DX3D	USIC0_CH0.DX4D	USIC0_CH1.DX5C
P2.9									VADC0.G0CH2		ERU0.3B0	USIC0_CH0.DX5A	USIC0_CH1.DX3B	USIC0_CH1.DX4B
P2.10	ERU0.PDOUT1	CCU40.OUT2	ERU0.GOUT1				USIC0_CH1.DOUT0		VADC0.G0CH3		ERU0.2B0	USIC0_CH0.DX3C	USIC0_CH0.DX4C	USIC0_CH1.DX0F
P2.11	ERU0.PDOUT0	CCU40.OUT3	ERU0.GOUT0			USIC0_CH1.SCLKOUT	USIC0_CH1.DOUT0		VADC0.G0CH4		ERU0.2B1	USIC0_CH1.DX0E	USIC0_CH1.DX1E	

Table 10 Hardware Controlled I/O Functions

Function	Outputs		Inputs		Pull Control			
	HWO0	HWO1	HWI0	HWI1	HW0_PD	HW0_PU	HW1_PD	HW1_PU
P0.0								
P0.1								
P0.2								
P0.3								
P0.4								
P0.5								
P0.6								
P0.7								
P0.8								
P0.9								
P0.10								
P0.11								
P0.12								
P0.13								
P0.14								
P0.15								
P1.0		USIC0_CH0. DOUT0		USIC0_CH0. HWIN0				
P1.1		USIC0_CH0. DOUT1		USIC0_CH0. HWIN1				
P1.2		USIC0_CH0. DOUT2		USIC0_CH0. HWIN2				
P1.3		USIC0_CH0. DOUT3		USIC0_CH0. HWIN3				
P1.4								
P1.5								
P1.6								
P2.0								
P2.1								
P2.2							$\overline{\text{CCU40.OUT3}}$	CCU40.OUT3
P2.3								
P2.4								

Table 10 Hardware Controlled I/O Functions

Function	Outputs		Inputs		Pull Control			
	HWO0	HWO1	HWI0	HWI1	HW0_PD	HW0_PU	HW1_PD	HW1_PU
P2.5								
P2.6							$\overline{\text{CCU40.OUT3}}$	CCU40.OUT3
P2.7							$\overline{\text{CCU40.OUT3}}$	CCU40.OUT3
P2.8							$\overline{\text{CCU40.OUT2}}$	CCU40.OUT2
P2.9							$\overline{\text{CCU40.OUT2}}$	CCU40.OUT2
P2.10								
P2.11								

3 Electrical Parameter

This section provides the electrical parameter which are implementation-specific for the XMC1100.

3.1 General Parameters

3.1.1 Parameter Interpretation

The parameters listed in this section represent partly the characteristics of the XMC1100 and partly its requirements on the system. To aid interpreting the parameters easily when evaluating them for a design, they are indicated by the abbreviations in the “Symbol” column:

- **CC**
  Such parameters indicate **C**ontroller **C**haracteristics, which are distinctive feature of the XMC1100 and must be regarded for a system design.
- **SR**
  Such parameters indicate **S**ystem **R**equirements, which must be provided by the application system in which the XMC1100 is designed in.

3.2 DC Parameters

3.2.1 Input/Output Characteristics

Table 16 provides the characteristics of the input/output pins of the XMC1100.

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Note: Unless otherwise stated, input DC and AC characteristics, including peripheral timings, assume that the input pads operate with the standard hysteresis.

Table 16 Input/Output Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Output low voltage on port pins (with standard pads)	V_{OLP}	CC	–	1.0	V	I_{OL} = 11 mA (5 V) I_{OL} = 7 mA (3.3 V)
			–	0.4	V	I_{OL} = 5 mA (5 V) I_{OL} = 3.5 mA (3.3 V)
Output low voltage on high current pads	V_{OLP1}	CC	–	1.0	V	I_{OL} = 50 mA (5 V) I_{OL} = 25 mA (3.3 V)
			–	0.32	V	I_{OL} = 10 mA (5 V)
			–	0.4	V	I_{OL} = 5 mA (3.3 V)
Output high voltage on port pins (with standard pads)	V_{OHP}	CC	V_{DDP} - 1.0	–	V	I_{OH} = -10 mA (5 V) I_{OH} = -7 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4.5 mA (5 V) I_{OH} = -2.5 mA (3.3 V)
Output high voltage on high current pads	V_{OHP1}	CC	V_{DDP} - 0.32	–	V	I_{OH} = -6 mA (5 V)
			V_{DDP} - 1.0	–	V	I_{OH} = -8 mA (3.3 V)
			V_{DDP} - 0.4	–	V	I_{OH} = -4 mA (3.3 V)
Input low voltage on port pins (Standard Hysteresis)	V_{ILPS}	SR	–	0.19 × V_{DDP}	V	CMOS Mode (5 V, 3.3 V & 2.2 V)
Input high voltage on port pins (Standard Hysteresis)	V_{IHPS}	SR	0.7 × V_{DDP}	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)

Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Pin capacitance (digital inputs/outputs)	C_{IO}	CC	–	10	pF	
Pull-up resistor on port pins	R_{PUP}	CC	20	50	kohm	$V_{IN} = V_{SSP}$
Pull-down resistor on port pins	R_{PDP}	CC	20	50	kohm	$V_{IN} = V_{DDP}$
Input leakage current[9)]	I_{OZP}	CC	-1	1	µA	$0 < V_{IN} < V_{DDP}$, $T_A \leq 105$ °C
Voltage on any pin during V_{DDP} power off	V_{PO}	SR	–	0.3	V	[10)]
Maximum current per pin (excluding P1, V_{DDP} and V_{SS})	I_{MP}	SR	-10	11	mA	–
Maximum current per high currrent pins	I_{MP1A}	SR	-10	50	mA	–
Maximum current into V_{DDP} (TSSOP28/16, VQFN24)	I_{MVDD1}	SR	–	130	mA	[10)]
Maximum current into V_{DDP} (TSSOP38, VQFN40)	I_{MVDD2}	SR	–	260	mA	[10)]
Maximum current out of V_{SS} (TSSOP28/16, VQFN24)	I_{MVSS1}	SR	–	130	mA	[10)]
Maximum current out of V_{SS} (TSSOP38, VQFN40)	I_{MVSS2}	SR	–	260	mA	[10)]

1) Rise/Fall time parameters are taken with 10% - 90% of supply.
2) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.150 ns/pF at 5 V supply voltage.
3) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.205 ns/pF at 3.3 V supply voltage.
4) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.445 ns/pF at 1.8 V supply voltage.
5) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.225 ns/pF at 5 V supply voltage.
6) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.288 ns/pF at 3.3 V supply voltage.
7) Additional rise/fall time valid for C_L = 50 pF - C_L = 100 pF @ 0.588 ns/pF at 1.8 V supply voltage.

Table 17 ADC Characteristics (Operating Conditions apply)[1)] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gain settings	G_{IN} CC		1		–	GNCTRxz.GAINy = 00_B (unity gain)
			3		–	GNCTRxz.GAINy = 01_B (gain g1)
			6		–	GNCTRxz.GAINy = 10_B (gain g2)
			12		–	GNCTRxz.GAINy = 11_B (gain g3)
Sample Time	t_{sample} CC	4	–	–	1 / f_{ADC}	V_{DD} = 5.0 V
		4	–	–	1 / f_{ADC}	V_{DD} = 3.3 V
		30	–	–	1 / f_{ADC}	V_{DD} = 2.0 V
Sigma delta loop hold time	t_{SD_hold} CC	20	–	–	µs	Residual charge stored in an active sigma delta loop remains available
Conversion time in fast compare mode	t_{CF} CC		9		1 / f_{ADC}	[2)]
Conversion time in 12-bit mode	t_{C12} CC		20		1 / f_{ADC}	[2)]
Maximum sample rate in 12-bit mode [3)]	f_{C12} CC	–	–	f_{ADC} / 43.5	–	1 sample pending
		–	–	f_{ADC} / 63.5	–	2 samples pending
Conversion time in 10-bit mode	t_{C10} CC		18		1 / f_{ADC}	[2)]
Maximum sample rate in 10-bit mode [3)]	f_{C10} CC	–	–	f_{ADC} / 41.5	–	1 sample pending
		–	–	f_{ADC} / 59.5	–	2 samples pending
Conversion time in 8-bit mode	t_{C8} CC		16		1 / f_{ADC}	[2)]

3.2.4 Power Supply Current

The total power supply current defined below consists of a leakage and a switching component.

Application relevant values are typically lower than those given in the following tables, and depend on the customer's system operating conditions (e.g. thermal connection or used application configurations).

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 19 Power Supply Parameters; V_{DDP} = 5V

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.[1]	Max.		
Active mode current Peripherals enabled f_{MCLK} / f_{PCLK} in MHz[2]	I_{DDPAE} CC	–	8.4	11.0	mA	32 / 64
		–	7.3	–	mA	24 / 48
		–	6.1	–	mA	16 / 32
		–	5.1	–	mA	8 / 16
		–	3.7	–	mA	1 / 1
Active mode current Peripherals disabled f_{MCLK} / f_{PCLK} in MHz[3]	I_{DDPAD} CC	–	4.7	–	mA	32 / 64
		–	4.1	–	mA	24 / 48
		–	3.3	–	mA	16 / 32
		–	2.6	–	mA	8 / 16
		–	1.5	–	mA	1 / 1
Active mode current Code execution from RAM Flash is powered down f_{MCLK} / f_{PCLK} in MHz	I_{DDPAR} CC	–	6.3	–	mA	32 / 64
		–	5.4	–	mA	24 / 48
		–	4.6	–	mA	16 / 32
		–	3.8	–	mA	8 / 16
		–	3.0	–	mA	1 / 1
Sleep mode current Peripherals clock enabled f_{MCLK} / f_{PCLK} in MHz[4]	I_{DDPSE} CC	–	5.9	–	mA	32 / 64
			5.4	–	mA	24 / 48
			4.8	–	mA	16 / 32
			4.3	–	mA	8 / 16
			3.7	–	mA	1 / 1

Table 20 provides the active current consumption of some modules operating at 5 V power supply at 25 °C. The typical values shown are used as a reference guide on the current consumption when these modules are enabled.

Table 20 Typical Active Current Consumption

Active Current Consumption	Symbol	Limit Values	Unit	Test Condition
		Typ.		
Baseload current	I_{CPUDDC}	5.04	mA	Modules including Core, SCU, PORT, memories, ANATOP[1)]
VADC and SHS	I_{ADCDDC}	3.4	mA	Set CGATCLR0.VADC to 1[2)]
USIC0	$I_{USIC0DDC}$	0.87	mA	Set CGATCLR0.USIC0 to 1[3)]
CCU40	$I_{CCU40DDC}$	0.94	mA	Set CGATCLR0.CCU40 to 1[4)]
WDT	I_{WDTDDC}	0.03	mA	Set CGATCLR0.WDT to 1[5)]
RTC	I_{RTCDDC}	0.01	mA	Set CGATCLR0.RTC to 1[6)]

1) Baseload current is measured with device running in user mode, MCLK=PCLK=32 MHz, with an endless loop in the flash memory. The clock to the modules stated in CGATSTAT0 are gated.

2) Active current is measured with: module enabled, MCLK=32 MHz, running in auto-scan conversion mode

3) Active current is measured with: module enabled, alternating messages sent to PC at 57.6kbaud every 200ms

4) Active current is measured with: module enabled, MCLK=PCLK=32 MHz, 1 CCU4 slice for PWM switching from 1500Hz and 1000Hz at regular intervals, 1 CCU4 slice in capture mode for reading period and duty cycle

5) Active current is measured with: module enabled, MCLK=32 MHz, time-out mode; WLB = 0, WUB = 0x00008000; WDT serviced every 1s

6) Active current is measured with: module enabled, MCLK=32 MHz, Periodic interrupt enabled

3.2.5 Flash Memory Parameters

Note: These parameters are not subject to production test, but verified by design and/or characterization.

Table 21 Flash Memory Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Erase Time per page / sector	t_{ERASE} CC	6.8	7.1	7.6	ms	
Program time per block	t_{PSER} CC	102	152	204	µs	
Wake-Up time	t_{WU} CC	–	32.2	–	µs	
Read time per word	t_a CC	–	50	–	ns	
Data Retention Time	t_{RET} CC	10	–	–	years	Max. 100 erase / program cycles
Flash Wait States [1]	$N_{WSFLASH}$ CC	0	0	0		f_{MCLK} = 8 MHz
		0	1	1		f_{MCLK} = 16 MHz
		1	1.3	2		f_{MCLK} = 32 MHz
Fixed Flash Wait States configured in bit NVM_NVMCONF.WS	$N_{FWSFLASH}$ SR	0	0	1		NVM_CONFIG1 .FIXWS = 1_B, $f_{MCLK} \leq$ 16 MHz
		1	1	1		NVM_CONFIG1 .FIXWS = 1_B, 16 MHz < $f_{MCLK} \leq$ 32 MHz
Erase Cycles	N_{ECYC} CC	–	–	$5*10^4$	cycles	Sum of page and sector erase cycles
Total Erase Cycles	N_{TECYC} CC	–	–	$2*10^6$	cycles	

1) Flash wait states are automatically inserted by the Flash module during memory read when needed. Typical values are calculated from the execution of the Dhrystone benchmark program.

Table 22 Power-Up and Supply Monitoring Parameters (Operating Conditions apply)[1)] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
V_{DDP} brownout reset voltage	V_{DDPBO} CC	1.55	1.62	1.75	V	calibrated, before user code starts running
V_{DDP} voltage to ensure defined pad states	V_{DDPPA} CC	–	1.0	–	V	
Start-up time from power-on reset	t_{SSW} SR	–	320	–	µs	Time to the first user code instruction in all start-up modes[4)]
BMI program time	t_{BMI} SR	–	8.25	–	ms	Time taken from a user-triggered system reset after BMI installation is is requested

1) Not all parameters are 100% tested, but are verified by design/characterisation.

2) A capacitor of at least 100 nF has to be added between V_{DDP} and V_{SSP} to fulfill the requirement as stated for this parameter.

3) Valid for a 100 nF buffer capacitor connected to supply pin where current from capacitor is forwarded only to the chip. A larger capacitor value has to be chosen if the power source sink a current.

4) This values does not include the ramp-up time. During startup firmware execution, MCLK is running at 32 MHz and the clocks to peripheral as specified in register CGATSTAT0 are gated.

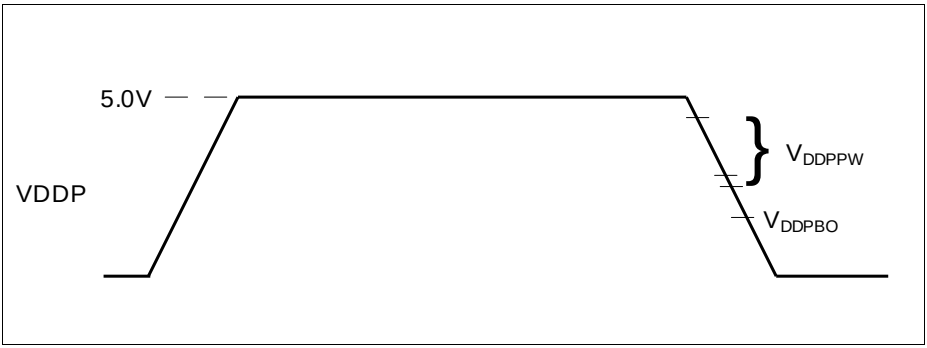


Figure 16 Supply Threshold Parameters

3.3.6 Peripheral Timings

Note: These parameters are not subject to production test, but verified by design and/or characterization.

3.3.6.1 Synchronous Serial Interface (USIC SSC) Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: Operating Conditions apply.

Table 27 USIC SSC Master Mode Timing

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
SCLKOUT master clock period	t_{CLK}	CC	62.5	–	–	ns	
Slave select output SELO active to first SCLKOUT transmit edge	t_1	CC	80	–	–	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t_2	CC	0	–	–	ns	
Data output DOUT[3:0] valid time	t_3	CC	-10	–	10	ns	
Receive data input DX0/DX[5:3] setup time to SCLKOUT receive edge	t_4	SR	80	–	–	ns	
Data input DX0/DX[5:3] hold time from SCLKOUT receive edge	t_5	SR	0	–	–	ns	

3.3.6.2 Inter-IC (IIC) Interface Timing

The following parameters are applicable for a USIC channel operated in IIC mode.

Note: Operating Conditions apply.

Table 29 USIC IIC Standard Mode Timing[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Fall time of both SDA and SCL	t_1 CC/SR	-	-	300	ns	
Rise time of both SDA and SCL	t_2 CC/SR	-	-	1000	ns	
Data hold time	t_3 CC/SR	0	-	-	µs	
Data set-up time	t_4 CC/SR	250	-	-	ns	
LOW period of SCL clock	t_5 CC/SR	4.7	-	-	µs	
HIGH period of SCL clock	t_6 CC/SR	4.0	-	-	µs	
Hold time for (repeated) START condition	t_7 CC/SR	4.0	-	-	µs	
Set-up time for repeated START condition	t_8 CC/SR	4.7	-	-	µs	
Set-up time for STOP condition	t_9 CC/SR	4.0	-	-	µs	
Bus free time between a STOP and START condition	t_{10} CC/SR	4.7	-	-	µs	
Capacitive load for each bus line	C_b SR	-	-	400	pF	

1) Due to the wired-AND configuration of an IIC bus system, the port drivers of the SCL and SDA signal lines need to operate in open-drain mode. The high level on these lines must be held by an external pull-up device, approximalely 10 kOhm for operation at 100 kbit/s, approximately 2 kOhm for operation at 400 kbit/s.

4 Package and Reliability

The XMC1100 is a member of the XMC™1000 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the exposed die pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

4.1 Package Parameters

Table 33 provides the thermal characteristics of the packages used in XMC1100.

Table 33 Thermal Characteristics of the Packages

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions	Ex × Ey CC	-	2.7 × 2.7	mm	PG-VQFN-24-19
		-	3.7 × 3.7	mm	PG-VQFN-40-13
Thermal resistance Junction-Ambient	$R_{\Theta JA}$ CC	-	104.6	K/W	PG-TSSOP-16-8[1)]
		-	70.3	K/W	PG-TSSOP-38-9[1)]
		-	46.0	K/W	PG-VQFN-24-19[1)]
		-	38.4	K/W	PG-VQFN-40-13[1)]

1) Device mounted on a 4-layer JEDEC board (JESD 51-5); exposed pad soldered.

Note: For electrical reasons, it is required to connect the exposed pad to the board ground V_{SSP}, independent of EMC and thermal requirements.

4.1.1 Thermal Considerations

When operating the XMC1100 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 115 °C.

The difference between junction temperature and ambient temperature is determined by $\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

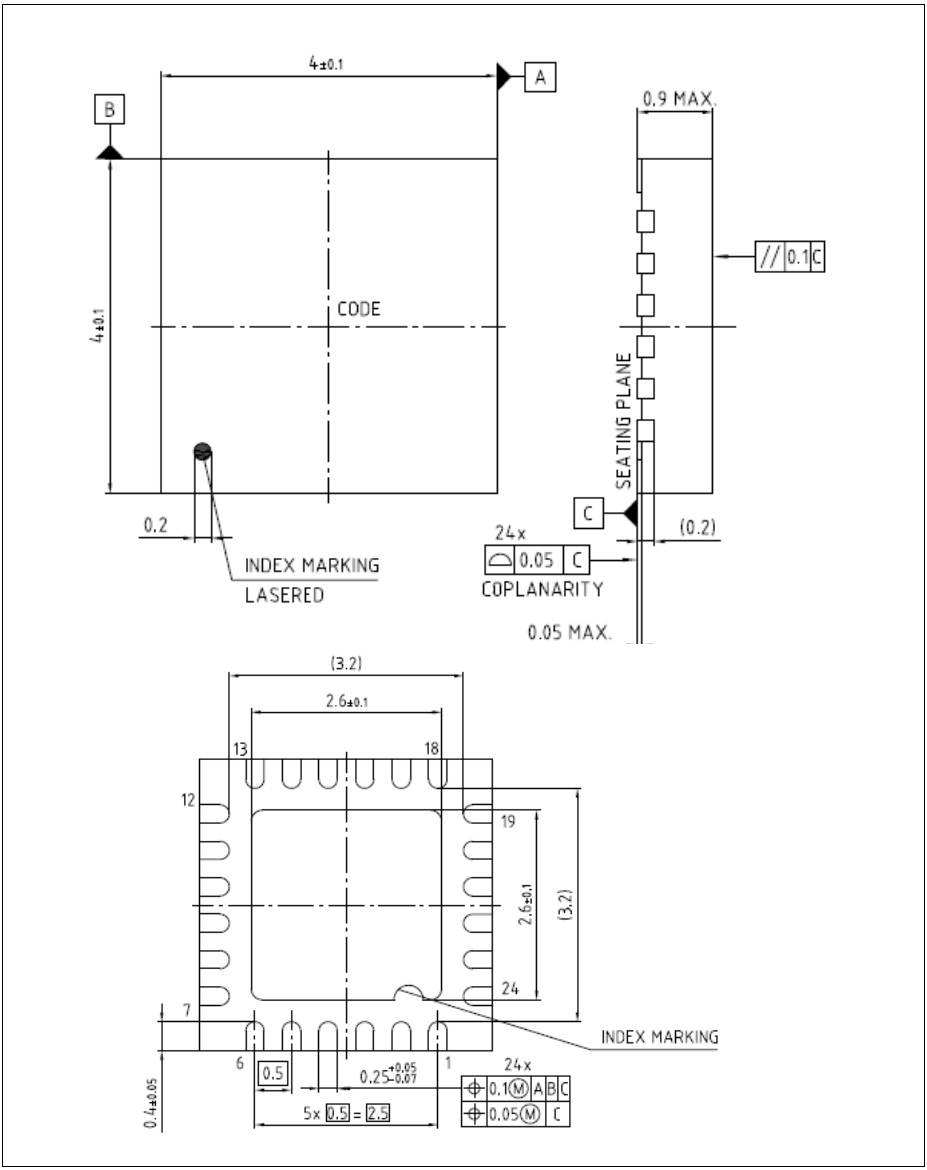


Figure 25 PG-VQFN-24-19